Features :

- Center amplifying gate
- Metal case with ceramic insulator
- Low on-state and switching losses

Typical Applications :

- AC controllers
- DC and AC motor control
- Controlled rectifiers

$I_{T(AV)}$	**3940A**
V_{DRM}/V_{RRM}	**1200 ～ 1800V**
I_{TSM}	**58 kA**
I^2t	**16820 10^3A^2S**

SYMBOL	CHARACTERISTIC	TEST CONDITIONS		T_j(℃)	VALUE			UNIT
					Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled,	T_C=70℃	125			3940	A
			T_C=55℃				4603	A
			T_C=85℃				3188	A
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}		125			250	mA
I_{TSM}	Surge on-state current	10ms half sine wave V_R=0V_{RRM}		125			58	kA
I^2t	I^2t for fusing coordination						16820	10^3A^2s
V_{TO}	Threshold voltage			125			0.77	V
r_T	On-state slope resistance						0.09	mΩ
V_{TM}	Peak on-state voltage	I_{TM}=5000A, F=63kN		25			1.60	V
dv/dt	Critical rate of rise of off-state voltage	V_{DM}=0.67V_{DRM}		125			1000	V/μs
di/dt	Critical rate of rise of on-state current	V_{DM}= 67%V_{DRM} to 2500A, Gate pulse t_r ≤0.5μs I_{GM}=1.5A.		125			200	A/μs
I_{GT}	Gate trigger current	V_A=12V, I_A=1A		25	40		300	mA
V_{GT}	Gate trigger voltage				0.8		3.0	V
I_H	Holding current				20		300	mA
I_L	Latching current						1500	mA
V_{GD}	Non-trigger gate voltage	V_{DM}=67%V_{DRM}		125			0.3	V
$R_{th(j-c)}$	Thermal resistance Junction to case	D.C. double side cooled Clamping force 63kN					0.0085	℃/W
$R_{th(c-h)}$	Thermal resistance case to heatsink						0.0020	
F_m	Mounting force				63		84	kN
T_{vj}	Junction temperature				-40		125	°C
T_{stg}	Stored temperature				-40		150	℃
W_t	Weight					1230		g
Outline	P73							

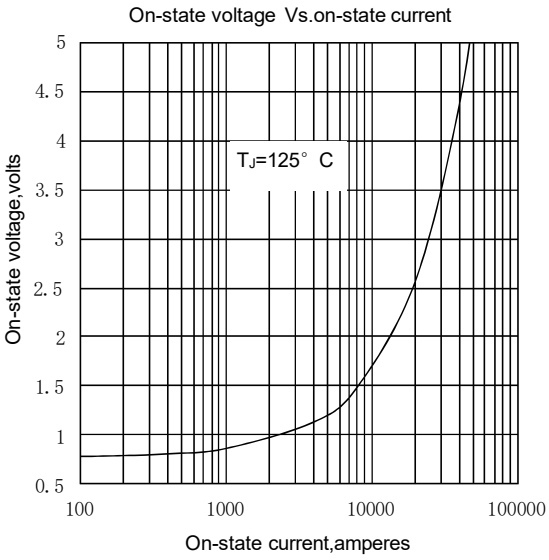

Fig.1

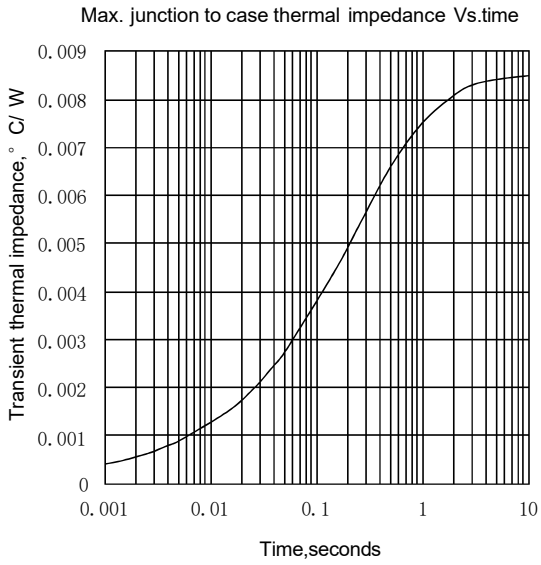

Fig.2

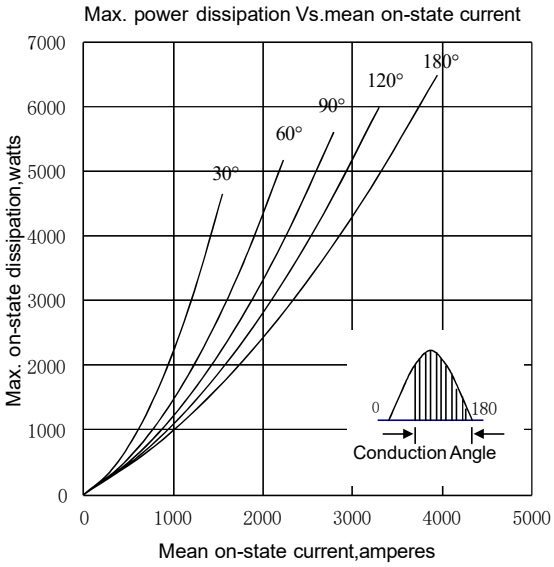

Fig.3

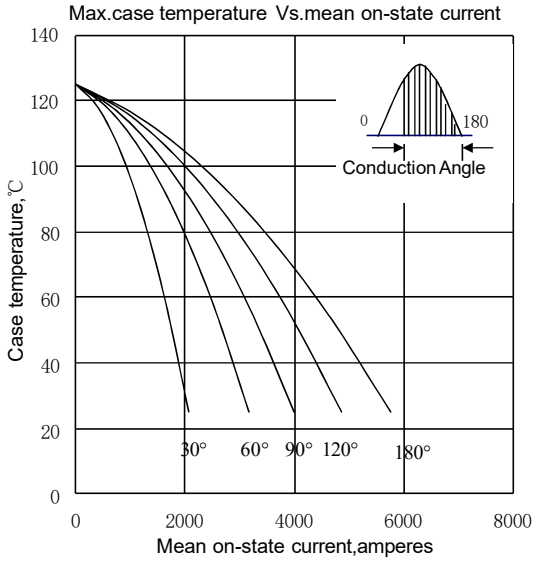

Fig.4

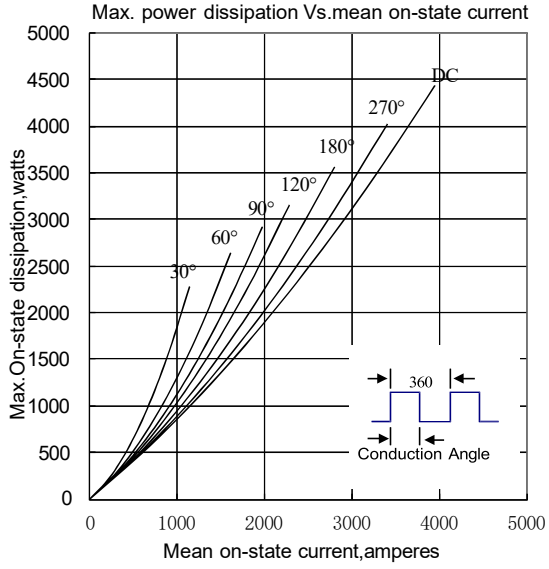

Fig.5

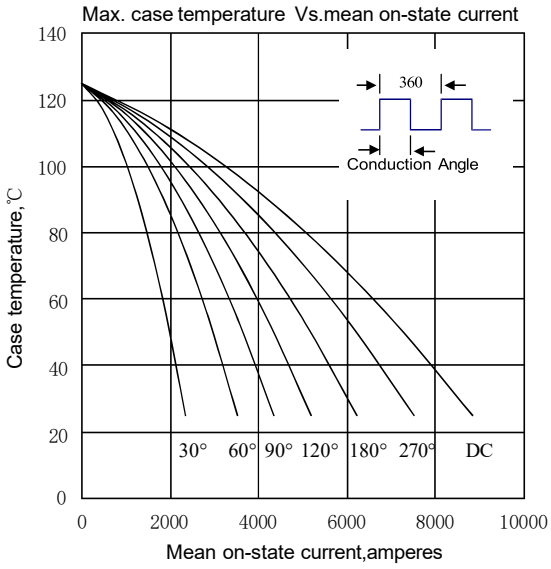

Fig.6

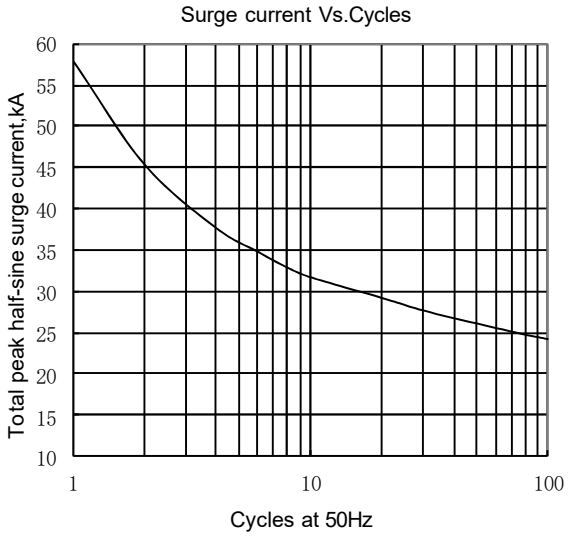

Fig.7

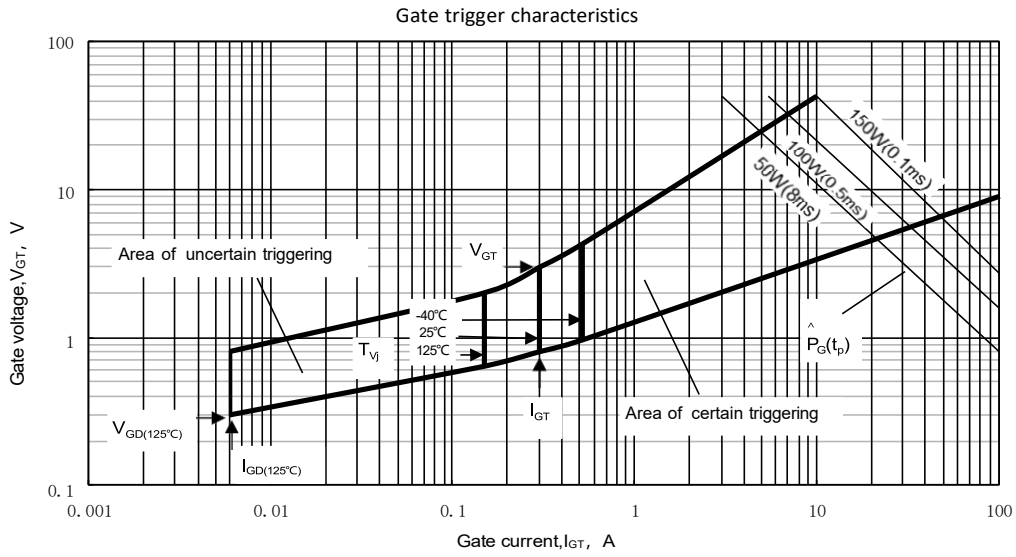

Fig.8

Outline: